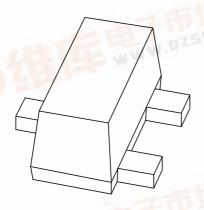
#### DISCRETE SEMICONDUCTORS

# DATA SHEET



## PDTC124TEF

NPN resistor-equipped transistor; R1 = 22 k $\Omega$ , R2 = open

**Product specification** 

2003 Jan 20







# NPN resistor-equipped transistor; R1 = 22 k $\Omega$ , R2 = open

#### PDTC124TEF

#### **FEATURES**

- Built-in bias resistors
- 250 mW total power dissipation
- Very small 1.6 mm × 0.85 mm thin package
- · Excellent coplanarity
- Flat leads
- Improved thermal behaviour
- Reduces number of components and required PCB area.

#### **APPLICATIONS**

- General purpose switching and amplification
- · Inverter and interface circuits
- · Circuit driver.

#### **DESCRIPTION**

NPN resistor equipped transistor in a SOT490 (SC-89) plastic package.

#### **MARKING**

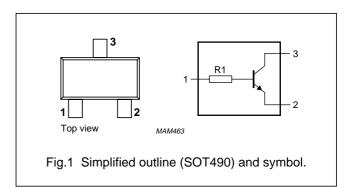
TYPE NUMBER	MARKING CODE			
PDTC124TEF	35			

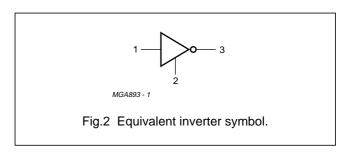
#### **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	MAX.	UNIT
$V_{CEO}$	collector-emitter voltage	50	V
I <sub>O</sub>	output current (DC)	100	mA
R1	bias resistor	22	kΩ
R2	open	_	_

#### **PINNING**

PIN	DESCRIPTION		
1	base/input		
2	emitter/ground (+)		
3	collector/output		





## NPN resistor-equipped transistor; R1 = 22 k $\Omega$ , R2 = open

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#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	_	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	_	50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	10	V
Io	output current (DC)		_	100	mA
I <sub>CM</sub>	peak collector current		_	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	_	250	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
T <sub>j</sub>	junction temperature		_	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C

#### Note

1. For mounting conditions, see "Thermal considerations and footprint design for SOT490 in the SC18 Data Handbook".

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	in free air; note 1	500	K/W

#### Note

1. For mounting conditions, see "Thermal considerations and footprint design for SOT490 in the SC18 Data Handbook".

#### **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	V <sub>CB</sub> = 50 V; I <sub>E</sub> = 0	_	_	100	nA
I <sub>CEO</sub>	collector-emitter cut-off current	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0	_	_	1	μΑ
		$V_{CE} = 30 \text{ V}; I_{B} = 0; T_{j} = 150 ^{\circ}\text{C}$	_	_	50	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0	_	_	100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 1 mA	100	_	_	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	_	_	150	mV
R1	input resistor		15.4	22	28.6	kΩ
C <sub>c</sub>	collector capacitance	$I_E = i_e = 0$ ; $V_{CB} = 10 \text{ V}$ ; $f = 1 \text{ MHz}$	_	_	2.5	pF

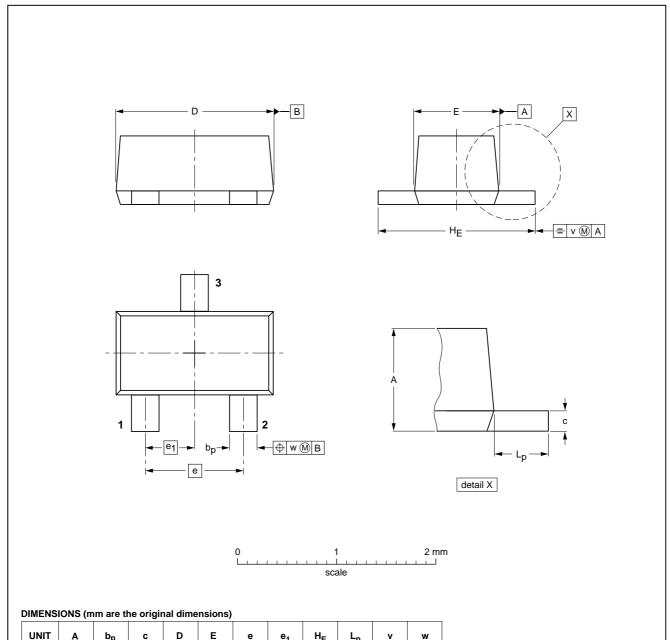
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#### **PACKAGE OUTLINE**

Plastic surface mounted package; 3 leads

SOT490



UNIT	A	bp	С	D	E	е	e <sub>1</sub>	HE	L <sub>p</sub>	v	w
mm	0.8 0.6	0.33 0.23	0.2 0.1	1.7 1.5	0.95 0.75	1.0	0.5	1.7 1.5	0.5 0.3	0.1	0.1

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC			ISSUE DATE	
SOT490			SC-89		$ \  \   \bigoplus  \bigoplus$	98-10-23

### NPN resistor-equipped transistor; R1 = 22 k $\Omega$ , R2 = open

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#### **DATA SHEET STATUS**

LEVEL	DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)(3)</sup>	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
III	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

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- 3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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**NOTES** 

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**NOTES** 

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#### **Contact information**

For additional information please visit http://www.semiconductors.philips.com. Fax: +31 40 27 24825 For sales offices addresses send e-mail to: sales.addresses@www.semiconductors.philips.com.

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Printed in The Netherlands

613514/01/pp8

Date of release: 2003 Jan 20

Document order number: 9397 750 10701

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